## **AMENDMENTS TO THE CLAIMS:**

1. (Original) An electronic device comprising:

an amorphous layer;

a MgO layer having a (001) orientation, wherein said MgO layer is formed on said amorphous layer;

a ReO<sub>3</sub> layer having a (001) orientation, wherein said ReO<sub>3</sub> layer is formed on said MgO layer; and

an oxide ferroelectric layer having a perovskite structure, said oxide ferroelectric layer being formed on said ReO<sub>3</sub> layer and having a (001) orientation.

- 2. (Canceled)
- 3. (Canceled)
- 4. (Original) The electronic device according to claim [[3]] 1, further comprising: an upper electrode formed on said oxide ferroelectric layer.
- 5. (Original) The electronic device according to claim 4,

wherein said amorphous layer is formed of an insulating layer, which is formed to cover a semiconductor element formed on a semiconductor substrate, and

a conductive plug is provided to electrically connect said semiconductor element, said conductive plug penetrating through said insulating layer.

- 6. (Original) The electronic device according to claim 5, wherein said ReO<sub>3</sub> layer is formed on said insulating layer and over said conductive plug.
- 7. (Original) The electronic device according to claim 5, further comprising: an interlayer insulating layer covering said upper electrode;

a plurality of apertures penetrating through said interlayer insulating layer and exposing said conductive plug and said upper electrode; and

a local wiring connecting said conductive plug and said upper electrode via said apertures.

- 8. (Original) The electronic device according to claim [[2]] 1, wherein said MgO layer is a single crystal MgO layer having a (001) plane.
- 9. (Original) The electronic device according to claim 1, wherein said ReO<sub>3</sub> layer is added with metal other than Re.
- 10. (Original) The electronic device according to claim 4, wherein said upper electrode is formed of an IrO<sub>2</sub> layer, or a stack of an IrO<sub>2</sub> layer and a SrRuO<sub>3</sub> layer.
- 11. (Withdrawn) A method of manufacturing an electronic device, comprising the steps of:
  - (a) preparing a ReO<sub>3</sub> layer having a (001) orientation; and
- (b) forming an oxide ferroelectric layer having a perovskite structure and a (001) orientation, on said ReO<sub>3</sub> layer.
- 12. (Withdrawn) The method of manufacturing an electronic device according to claim
- 11, wherein said step(a) deposits said ReO<sub>3</sub> layer on a single crystal MgO layer having the (001) orientation.
- 13. (Withdrawn) The method of manufacturing an electronic device according to claim 11, wherein said step (a) includes the steps of:
- (a-1) preparing a MgO layer having a (001) orientation; and (a-2) forming said ReO<sub>3</sub> layer having a (001) orientation on said MgO layer.

14. (Withdrawn) The method of manufacturing an electronic device according to claim13, wherein said step (a-1) includes the steps of:

(a-1-1) preparing an amorphous layer; and

- (a-1-2) forming said MgO layer having a (001) orientation on said amorphous layer.
- 15. (Withdrawn) The method of manufacturing an electronic device according to claim 14, wherein at least one of said steps (a-1-2), (a-2) and (b) is done by metalorganic chemical vapor deposition (MOCVD).
- 16. (Withdrawn) The method of manufacturing an electronic device according to claim 15, wherein all of said steps (a-1-2), (a-2) and (b) are done by MOCVD.
- 17. (Withdrawn) The method of manufacturing an electronic device according to claim 15, wherein said MOCVD is executed at a substrate temperature of 620°C or lower.
- 18. (Withdrawn) . The method of manufacturing an electronic device according to claim 15, wherein said MOCVD uses, as organometal raw material, a dipivaloilmethanate (DPM) compound of metal or an iso-proxy (i-PrO) compound of metal.
- 19. (Withdrawn) The method of manufacturing an electronic device according to claim 14, wherein at least one of said steps (a-1-2), (a-2) and (b) is done by sputtering.
- 20. (Withdrawn) The method of manufacturing an electronic device according to claim 11, further comprising the step of: (c) forming at least one upper electrode layer on said oxide ferroelectric layer.